Photolithography II

- Basics
- · Nature of light
- "Steppers"
- · Contact Printing
- Alignment
 - Marks
 - Errors
 - Design Rules
- · Lithography Trends

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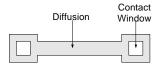
Basics

- Resolution
 - Simply put the smallest feature that can be resolved. Ultimately, it is not just home thin a line of PR we can pattern, but also how thin we can carry out our process
 - Diffusion under masks
 - Undercutting of masks
- Pattern registration
- Throughput

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Basics

- Pattern registration
 - How well can a previous mask step be fit to to following mask step.



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Basics

- Throughput
 - This is a measure of how many wafers you can pattern per unit time.
 - For instance: I am down to 3 minutes per 4" wafer including exposure time with 99% accuracy. What if I could go faster, but my accuracy dropped? How would you determine which was more cost effective?

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Photolithography

- Nature of light
 - Light can behave as if it were a particle and as if it were a wave.
 - Depending on the type of photolithography exposure system will dictate how you have to treat light in your model.

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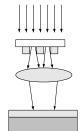
Photolithography
Coherent illumination

Fresnel region of diffraction

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"Steppers"

- The Mask is separated from the wafer
- The image is reduced (makes it easier to make Lens a mask)
- The same pattern is stepped over the entire surface automatically



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"Steppers"

- Expensive to maintain
- Susceptible to lens errors

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Contact Printing

- Inexpensive, but not automatic.
- The features have to be the same size on the mask as the are on the wafer.
- The mask are in contact with the PR which can cause damage to the masks.

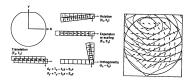
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Alignment

 This is the ability to successfully line up successive features on a wafer. What would happen if the gate metal were placed over the S or D contacts?



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Alignment

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Aligned

Substrate

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Lithography Trends

- E-Beam
 - Electron beams have a large energy or small wavelength, but have to be scanned across the wafer, not flood exposed
- · Deep UV or Soft x-ray
 - Lenses can still be used to focus light as is a stepper reduction system
- · X-ray
 - Back to Contact Printing?

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